

Superconductivity in a strongly correlated one-band system

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We study superconductivity in the extended Hubbard model with a strong on-site repulsion U and weak attractive density-density interaction V_{ij} . The electron correlation effects, beyond the weak-coupling regime of U , are included approximately by employing Hubbard decoupling approximations. The formulas for superconducting transition temperature T_c of the present approach are compared to those obtained with the strong-coupling expansion and slave-boson techniques. The methods share some common features. We discuss behavior of T_c for superconducting phases with s - and d -wave symmetry of the superconducting order parameter. In contrast to the mean-field treatment of U , we find that the strong on-site repulsion does not destroy superconductivity induced by $V_{ij} < 0$ even when $U \gg |V_{ij}|$. [S0163-1829(96)02929-3]

Study of superconductivity in strongly correlated electron systems in narrow energy bands has been pursued with renewed interest since the discovery of high- T_c cuprate oxides.¹ Most of these studies are based on the premise that a single band or extended Hubbard-type models can be used to capture the physics of high- T_c cuprate superconductors.² The methods employed range from broken symmetry mean-field approximations through various decoupling approximation schemes, canonical transformations, $1/N$ expansions, to slave-fermion or slave-boson techniques. Still, there is no unambiguous proof that superconducting correlations strong enough to lead to high- T_c 's arise from strong on-site repulsion in a single band Hubbard model. It is now well accepted that Coulomb interaction on the Cu sites in high- T_c cuprate oxides is strong enough to split-off the uncorrelated Cu- d band into Hubbard subbands and that superconducting pairing occurs in the less than half-filled Hubbard subband. A theoretical study of superconducting pairing in the Hubbard subbands is, then, of considerable interest. In this paper, we present such an investigation employing an extended Hubbard model with strong on-site repulsive and weak attractive intersite interactions (U and V_{ij} , respectively). We employ the Hubbard subband operator approach³⁻⁵ to include the many-body correlations arising from the strong on-site repulsive interaction U . We will also compare our results with those obtained using strong-coupling canonical expansion⁶ and slave-boson^{7,8} methods.

We take the Hamiltonian in the following form:

$$H = - \sum_{i,j,\sigma} t_{ij} c_{i\sigma}^\dagger c_{j\sigma} + U \sum_i n_{i\downarrow} n_{i\uparrow} + \sum_{i,j} \sum_{\sigma,\sigma'} V_{ij} n_{i\sigma} n_{j\sigma'} - \mu \sum_{i,\sigma} n_{i\sigma}. \quad (1)$$

Further on the V_{ij} term is assumed to be at least an order of magnitude smaller than U . This model has been previously studied by Micnas *et al.*⁶ in both weak- ($U \ll t$) and strong-

coupling ($U \gg t$) limits. It has also been qualitatively analyzed in the Hubbard-Jain approach.^{4,5} However, no explicit calculations have been performed so far. In all cases we assume $|V| \ll W$, ($W = 8t$ and V is interaction between the nearest sites in $2d$ square lattice) so that the Hartree-Fock-Bogoliubov factorization for that part of Hamiltonian is legitimate.

To start let us recall the strong-coupling limit of the Hamiltonian (1). To leading order in $1/U$ it reads^{6,9}

$$H_{\text{eff}} = - \sum_{i,j,\sigma} t_{ij} h_{i\sigma}^\dagger h_{j\sigma} + \sum_{i,j} J_{ij} \left(\vec{S}_i \cdot \vec{S}_j - \frac{1}{4} N_i N_j \right) + \sum_{i,j} V_{ij} N_i N_j - \mu \sum_{i,\sigma} n_{i\sigma}, \quad (2)$$

where $h_{i\sigma} = c_{i\sigma}(1 - n_{i-\sigma})$, $N_{i\sigma} = h_{i\sigma}^\dagger h_{i\sigma} = n_{i\sigma}(1 - n_{i-\sigma})$, $N_i = \sum_\sigma N_{i\sigma}$, $S_i^+ = c_{i\uparrow}^\dagger c_{i\downarrow}$, $S_i^z = \frac{1}{2}(n_{i\uparrow} - n_{i\downarrow})$ and $J_{ij} = 2t_{ij}^2/U$. Terms corresponding to hopping of nearest-neighbor electron pairs are not taken into account.

Gorkov-type factorization leads to the BCS-like equation for the gap function⁶

$$\Delta_k = \frac{1}{N} \sum_q V_{kq} \frac{\Delta_q}{2E_q} \tanh\left(\frac{\beta E_q}{2}\right) \quad (3)$$

with $E_q = \sqrt{\xi_q^2 + |\Delta_q|^2}$ and $\xi_q = \delta \cdot \varepsilon_q - \bar{\mu}$ and $\delta = 1 - n$ (n is the electron concentration). An important point of this approach is the renormalization of charge-charge interaction $V_{kq} = V \delta \gamma_{k-q}$ through the factor δ . Such a term, as we shall see, is absent in the mean-field approximation to the slave-boson method.

The use of the slave-boson method is particularly simple in the $U = \infty$ limit. Electron configurations of a system (for $n < 1$) can under such circumstances consist only of singly occupied and empty sites. No double occupancy is allowed. One replaces the electron operators ($c_{i\sigma}$) via new fermion ($f_{i\sigma}$) and auxiliary bose field (b_i) operators. The require-

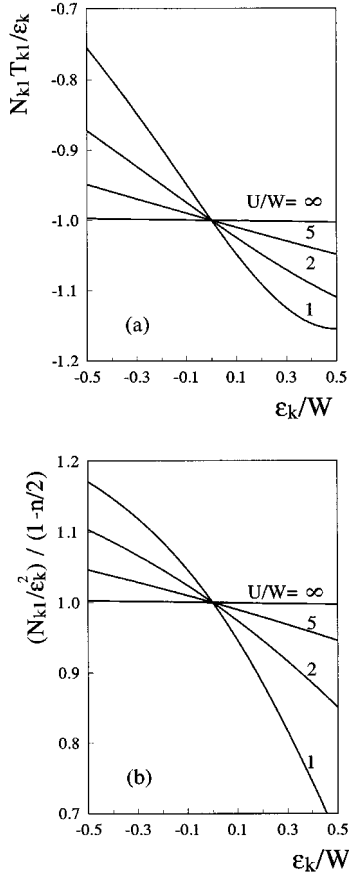


FIG. 1. Plot of the $N_{kl}T_{kl}/\epsilon_k$ function (a) and the normalized N_{kl}/ϵ_k^2 function (b) versus single-particle energy ϵ_k for several values of U .

ment of no double occupation in this limit is fulfilled with the introduction of a term into the Hamiltonian which constrains the allowed states. One gets a Hamiltonian in the form

$$H^{SB} = - \sum_{i,j,\sigma} t_{ij} f_{i\sigma}^\dagger f_{j\sigma} b_i^\dagger b_j - \mu \sum_{i\sigma} f_{i\sigma}^\dagger f_{i\sigma} + \sum_{i,j} V_{ij} n_i n_j + \sum_i \lambda_i \left(\sum_{\sigma} f_{i\sigma}^\dagger f_{i\sigma} + b_i^\dagger b_i - 1 \right). \quad (4)$$

Here $n_i = \sum_{\sigma} f_{i\sigma}^\dagger f_{i\sigma}$, and λ_i denotes the Lagrange multiplier. The mean field for slave bosons means¹⁰ replacement of all bosonic fields by their classic values $b_i = b_i^\dagger = r$ and $\lambda_i = \lambda$. Parameters λ and r are determined by minimization of the ground-state energy ($E = \langle H \rangle$) of the system. This leads to $r^2 = 1 - n$ and $\lambda = - \sum_k n_{k\sigma} \epsilon_k$.

A standard Gorkov-type procedure allows a derivation of the formula (3) with $V_{k-q} = V \gamma_{k-q}$ and $\xi_k = r^2 \epsilon_k - \mu + \lambda + 2nV$. Thus the two approaches differ with respect to renormalization of interaction V_{kq} and additional shift λ of the spectrum. In the slave-boson approach the renormalization of interaction does not appear while in the canonical transformation method the term δ is introduced in order to get the correct $\delta \rightarrow 0$ limit.

The Hubbard subband operator approach^{3,4} relies on the introduction of new operators $d_{i\sigma}^\alpha = n_{i-\sigma}^\alpha c_{i\sigma}$ and their conju-

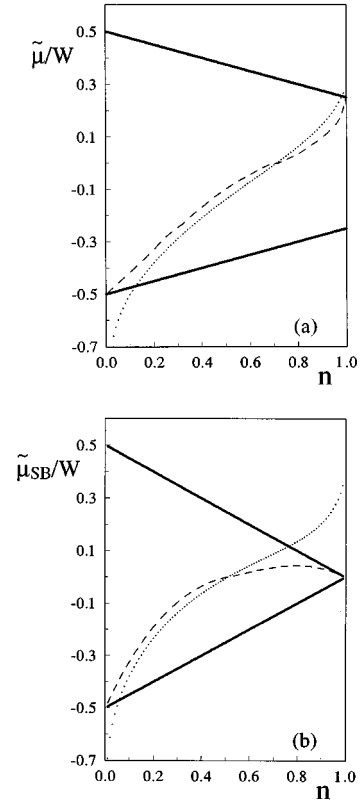


FIG. 2. Position of a chemical potential $\tilde{\mu}$ in the effective lower Hubbard subband obtained by the Hubbard-Jain method (a) and in the effective band by the slave-boson method (b). The dashed lines correspond to zero temperature while dotted ones to $T = 0.1W$.

gate counterparts $d_{i\sigma}^{\alpha\dagger} = (d_{i\sigma}^\alpha)^\dagger$, where $n_{i\sigma}^1 = 1 - n_{i\sigma}$ and $n_{i\sigma}^2 = n_{i\sigma}$. One writes then the equation of motion for these new operators. Using again Gorkov-type decoupling and Fourier transformation one gets⁵

$$\omega d_{k\sigma}^\alpha = (\epsilon_\alpha - \tilde{\mu}) d_{k\sigma}^\alpha + n^\alpha \epsilon_k c_{k\sigma} + c_{-k-\sigma}^\dagger \sum_{k'} \left[(-1)^\alpha (\epsilon_k + 2\epsilon_{k'}) + 2n^\alpha \sum_{k'} V_{k-k'} \right] \times \langle c_{-k'-\sigma} c_{k'\sigma} \rangle \quad (5)$$

with $\tilde{\mu} = \mu - 8nV$. At this step it is convenient to introduce the ‘‘Hubbard subband’’ operators $D_{k\sigma}^\nu = (N_{k\nu}/\epsilon_k) [d_{k\sigma}^1/E_{k\nu} + d_{k\sigma}^2/(E_{k\nu} - U)]$ where $E_{k\nu}$ are solutions of the Hubbard I problem

$$E_{k\nu} = \frac{1}{2} [U + \epsilon + (-1)^\nu \sqrt{(U - \epsilon_k)^2 + 2nU\epsilon_k}] \quad (6)$$

and

$$N_{k\nu} = \left[\frac{n/2}{(E_{k\nu} - U)^2} + \frac{1-n/2}{E_{k\nu}^2} \right]^{-1}. \quad (7)$$

The subband operators obey the following equation of motion:

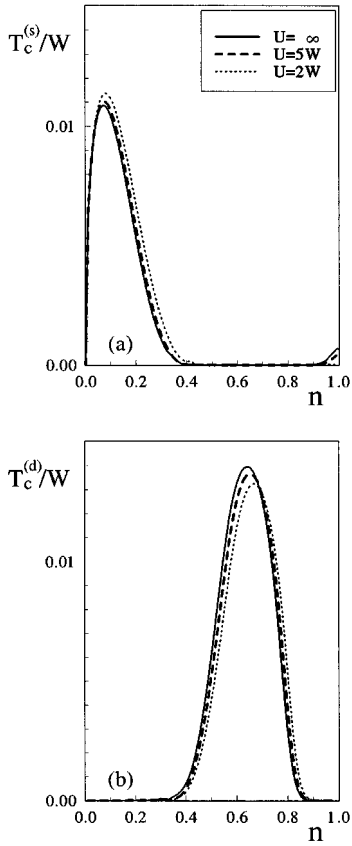


FIG. 3. Critical temperature for the s -wave superconducting state (a) and d -wave superconducting state (b) as a function of total carrier concentration $n = \langle n_{i\sigma} \rangle + \langle n_{i-\sigma} \rangle$. Strength of intersite attraction is in all cases the same and equal $V = -0.1W$. Values of U for particular curves are shown in the legend.

$$\omega D_{k\sigma}^v = (E_{kv} - \tilde{\mu}) D_{k\sigma}^v + \Delta_{kv} \sum_{\nu'=1,2} D_{-k-\sigma}^{\nu'\dagger}. \quad (8)$$

Neglecting nondiagonal correlation functions, we arrive at the gap equation

$$\Delta_{kv} = \sum_{k'} \left[\frac{T_{kv} N_{kv}}{\varepsilon_k} (\varepsilon_k + 2\varepsilon_{k'}) + \frac{N_{kv}}{\varepsilon_k^2} 2V_{k-k'} \right] \langle D_{-k'-\sigma}^v D_{k'\sigma}^v \rangle, \quad (9)$$

where $T_{kv} = U/[E_{kv}(E_{kv} - U)]$. The gap equation (9) looks a little bit more complicated than that given previously (3). For comparison with the previous formulas let us evaluate it in the leading order with respect to $1/U$. In doing so we have to take into account that in the large- U limit ($U \rightarrow \infty$) the on-site pairing is prohibited. So we neglect all the terms which would lead to the formation of such pairs. Finally, for $n < 1$ and for $U \rightarrow \infty$, we obtain that Δ_{k1} is expressed by Eq. (3) with $V_{kq} = (1 - n/2)^2 V \gamma_{k-q}$ and $\xi_q = \varepsilon_q (1 - n/2) - \tilde{\mu}$.

Thus the Hubbard-subband-operator method leads in a natural way to renormalization of both: the single-particle energies and interactions. Renormalization of energies, however, does not lead to vanishing of the bandwidth at $n = 1$. Further analytical comparison is a little bit complicated because in each case a position of the Fermi level has to be calculated for a given carrier concentration. For example, for

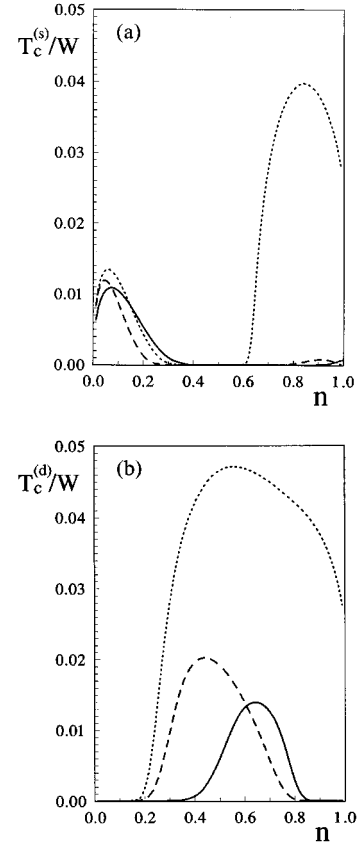


FIG. 4. Comparison of transition temperatures of s -wave (a) and d -wave (b) superconducting phases for the extended Hubbard model with $U = \infty$ and $V = -0.1W$. Solid lines refer to the Hubbard-Jain approximation, dashed ones to those obtained according to canonical transformation method⁶ and dotted ones to the slave-boson approach.

$U \gg W$, the position of the Fermi level in the lower Hubbard subband ($n < 1$) is given by the formula

$$\frac{n}{2} = \left(1 - \frac{n}{2} \right) \sum_k f[(1 - n/2)\varepsilon_k - \tilde{\mu}], \quad (10)$$

where $f(x) = 1/(e^{\beta x} + 1)$ is the Fermi-Dirac distribution function.

For a numerical illustration of our results for the model (1) with arbitrary U , we use the general form of the gap equation (9). The \vec{k} -dependent gap function takes then the following form:

$$\Delta_{kv} = \frac{T_{kv} N_{kv}}{\varepsilon_k} \Delta_v^{(0)} + \frac{N_{kv}}{\varepsilon_k^2} \Delta_v^{(s)} \varepsilon_k + \frac{N_{kv}}{\varepsilon_k^2} \Delta_v^{(d)} \eta_k, \quad (11)$$

where $\varepsilon_k = -2t(\cos k_x + \cos k_y)$, $\eta_k = -2t(\cos k_x - \cos k_y)$. Here $\Delta_v^{(0)}$, $\Delta_v^{(s)}$, and $\Delta_v^{(d)}$ refer to isotropic and extended s -wave or d -wave symmetry gap functions, respectively. The additional factors in front of them depend on \vec{k} through ε_k only, and for $U > W$ are relatively slowly varying functions. Their dependence on ε_k for various values of U is shown in Fig. 1. With increasing U , both factors tend to their asymptotic values $[(T_{k1} N_{k1} / \varepsilon_k) \xrightarrow{U \rightarrow \infty} -1, (N_{k1} / \varepsilon_k^2) \xrightarrow{U \rightarrow \infty} 1 - n/2]$.

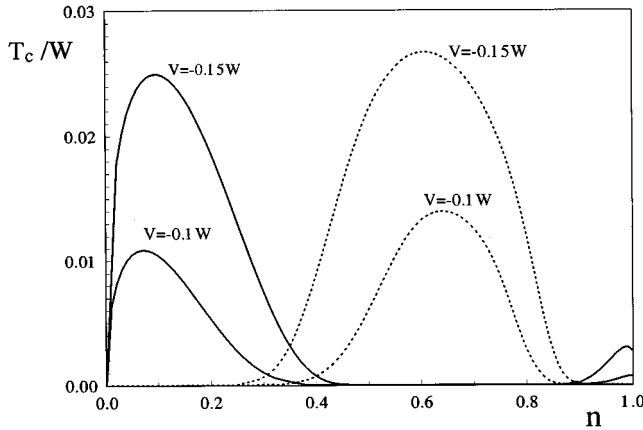


FIG. 5. Influence of the pairing potential V on the carrier dependence of $T_c^{(s)}$ (solid lines) and $T_c^{(d)}$ (dotted lines). The on-site interaction is in this case $U=10W$.

To get carrier concentration dependence of the transition temperature it is necessary to solve the gap equation self-consistently with the equation for chemical potential $\tilde{\mu}$. The dependence of $\tilde{\mu}$ on n is shown in Fig. 2(a). The thick lines denote edges of the lower subband, the dashed line shows $\tilde{\mu}$ for $T=0$ K and the dotted line at $T=0.1W$. Figure 2(b) shows $\tilde{\mu}_{\text{SB}} = \mu - \lambda - 2nV$. Note, that for $n=1$, the bandwidth vanishes in the slave-boson method.

The concentration dependences of $T_c^{(s)}$ and $T_c^{(d)}$ are plotted in Figs. 3(a) and 3(b), respectively, for a number of U values. Coulomb repulsion U has a small detrimental effect on the s -wave superconducting phase at low concentrations but $T_c^{(s)}$ remains finite (nonzero) even for $U=\infty$ (solid line). At low hole concentrations ($n\sim 1$) there appears also another s -wave superconducting phase with very small $T_c^{(s)}$, which is relatively stable against U values. In fact, transition temperatures in that region increase with increasing U . The main effect of U on the d phase is a slight shift of maximal

$T_c^{(d)}$ towards the lower concentrations n . The maximal value of $T_c^{(d)}$ surprisingly increases with increasing U .

Figure 4(a) shows the comparison of $T_c^{(s)}(n)$ calculated in the Hubbard-Jain approximation (solid line), strong-coupling expansion method (dashed line), and slave-boson approach (dotted line). Figure 4(b) presents similar data for $T_c^{(d)}(n)$.

It is important to note that in our approach the superconducting phase appears only for attractive interaction V . It is in contrast to slave-boson treatment of the present system⁷ which, for finite U , leads to superconductivity even with repulsive V . Influence of the V strength on the magnitude of T_c is shown in Fig. 5. As is seen, values of critical temperatures considerably increase with increasing intersite attraction.

In conclusion, we have presented a study of the many-body effects of strong on-site repulsion U on BCS pairing in the extended Hubbard model. Contrary to the results in a Hartree-Fock treatment of U , we find that the strong U does not destroy the superconducting state produced by the weak intersite attractive interaction V . The s -wave superconductivity appears in the dilute regions (at small electron and small hole concentrations), while the d -wave phase arises around $\delta=0.33$, and for $V=-0.1W$ extends from $\delta\approx 0.15$ to $\delta\approx 0.6$. The maximal value of $T_c^{(d)}$ surprisingly increases with increasing U . It follows from this study as well as previous treatments of the correlated hopping model^{11,12} by the same technique, that the main effect of on-site interaction U is a formation of Hubbard subbands and the BCS pairing occurs between the quasiparticles in the Hubbard subbands.

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